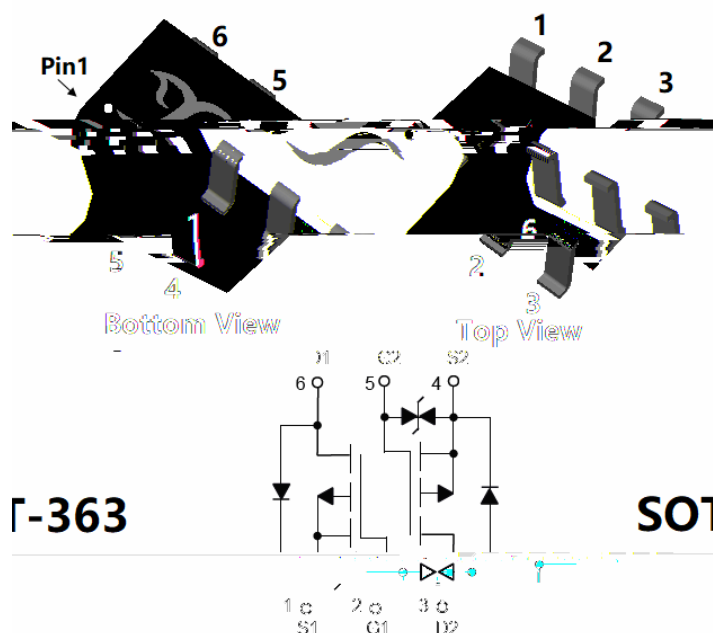


YJL3139KADW



- $R_{DS(ON)}$ (at $V_{GS}=-2.5V$) 850 mohm
- $R_{DS(ON)}$ (at $V_{GS}=-1.8V$) 1200 mohm
- $R_{DS(ON)}$ (at $V_{GS}=-1.8V$) 2000 mohm
- ESD Protected Up to 2.0KV (HBM)

General Description

- Trench Power LV MOSFET technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed switching

Applications

- Interfacing, Logic switch
- Load switch
- Power management

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter		Symbol	Maximum	Unit
Drain-source Voltage		V_{DS}	-20	V
Gate-source Voltage		V_{GS}	12	V
Drain Current	$T_A=25$ Steady State	I_D	-0.5	A
	$T_A=70$ Steady State		-0.4	
Pulsed Drain Current ^A		I_{DM}	-2.6	A
Total Power Dissipation @ $T_A=25$ Steady State		P_D	0.15	W
Thermal Resistance Junction-to-Ambient @ Steady State ^B		$R_{\theta JA}$	833	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150	

YJL3139KADW	F2e 39K Ae	3000e 30000e	e	"		



■ Electrical Characteristics ($T_J=25$

■ Typical Performance Characteristics

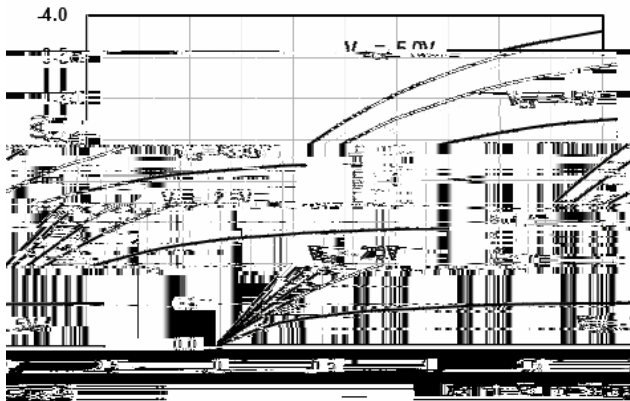


Figure1. Output Characteristics

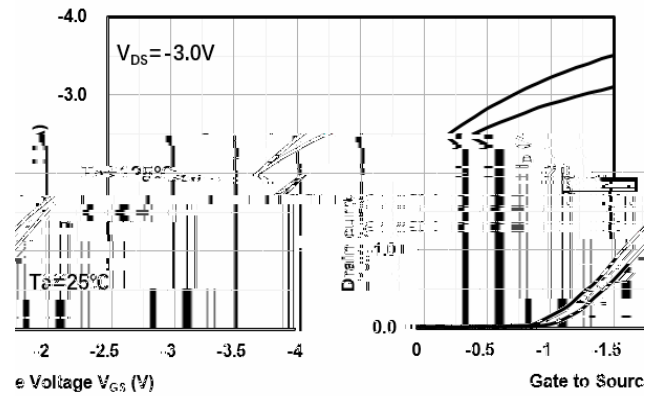


Figure2. Transfer Characteristics

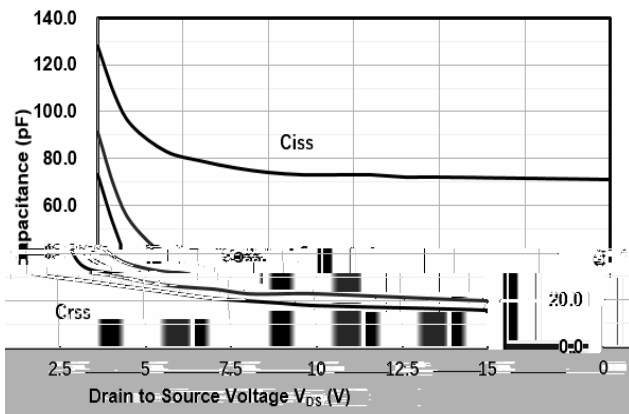


Figure3. Capacitance Characteristics

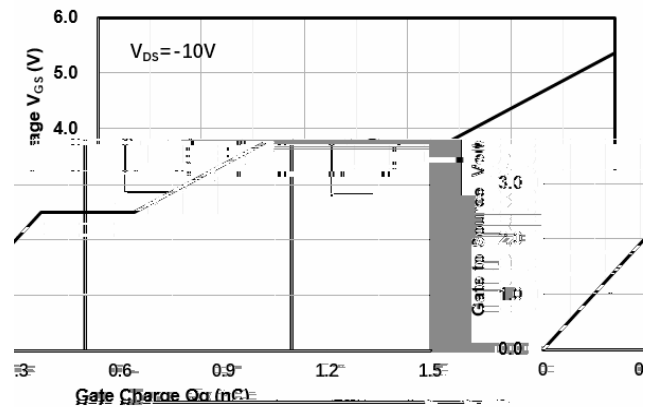


Figure4. Gate Charge

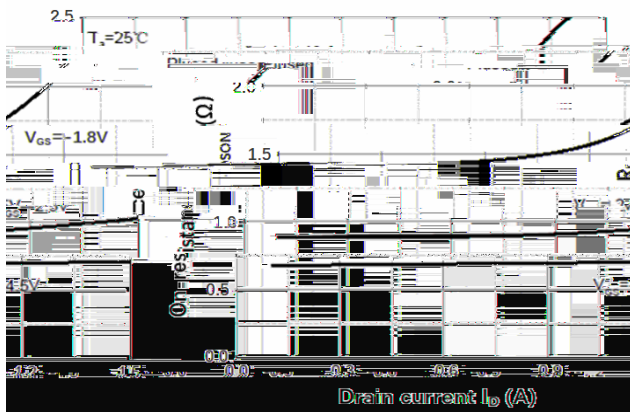


Figure5. Drain-Source on Resistance

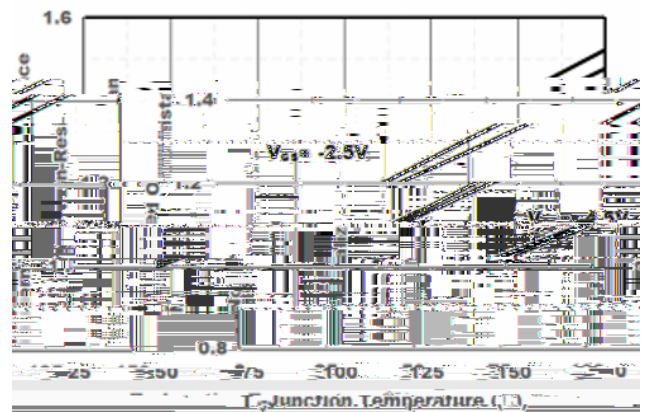


Figure6. Drain-Source on Resistance

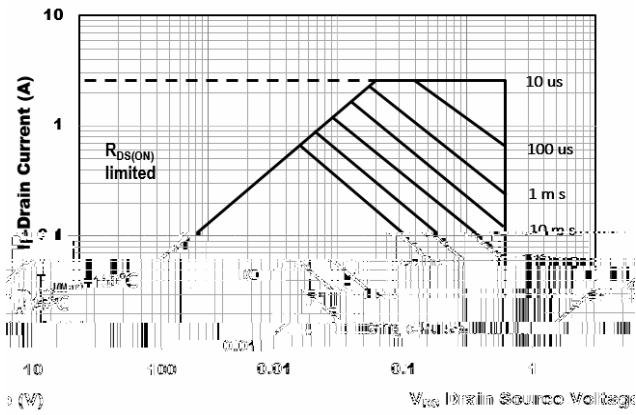


Figure7. Safe Operation Area

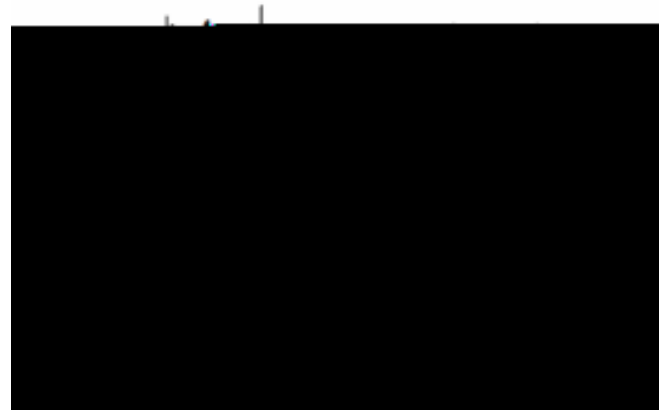


Figure8. Switching wave

< - / . \$ ' :

v 6 2 7 3 D F N D J H L Q I R U P D W L R Q

